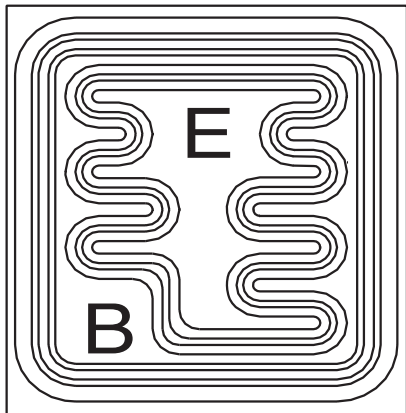


**PROCESS DETAILS**

Process	EPITAXIAL PLANAR
Die Size	16.5 x 16.5 MILS
Die Thickness	9.0 MILS
Base Bonding Pad Area	3.5 x 4.3 MILS
Emitter Bonding Pad Area	3.5 x 4.3 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

**GEOMETRY**



BACKSIDE COLLECTOR

**GROSS DIE PER 4 INCH WAFER**

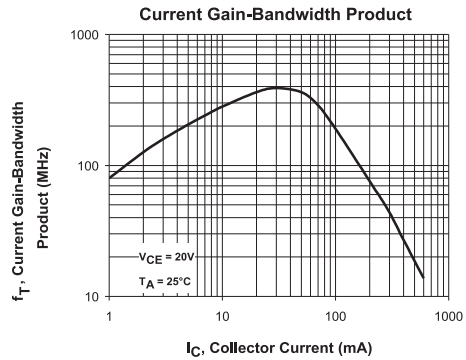
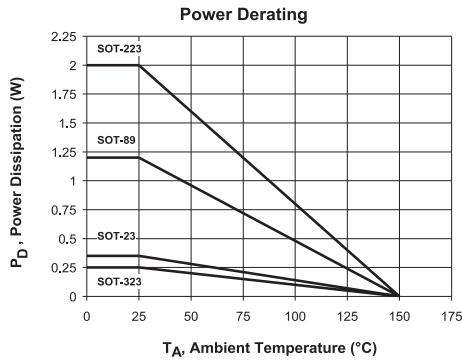
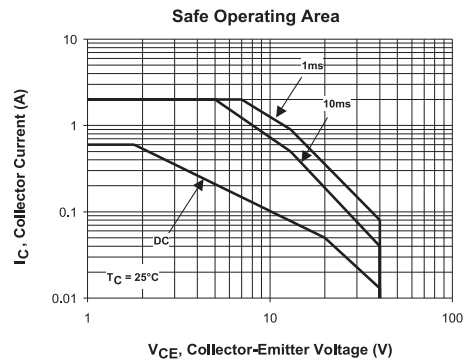
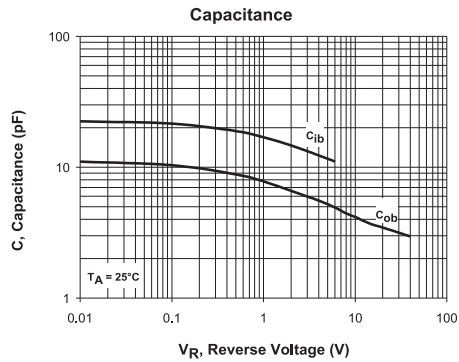
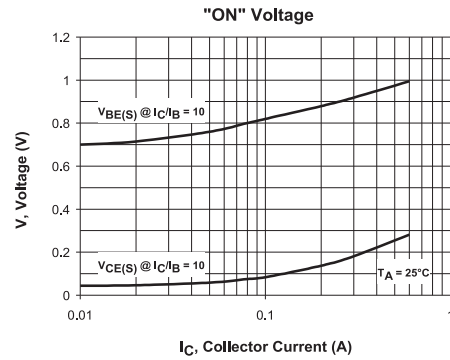
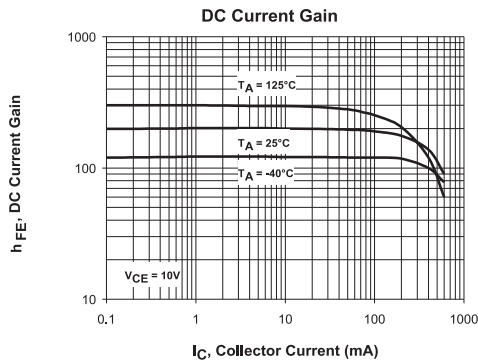
41,690

**PRINCIPAL DEVICE TYPES**

2N2219A  
2N2222A  
CMPT2222A  
CMST2222A  
CXT2222A  
CZT2222A  
MD2219A  
PN2222A

145 Adams Avenue  
Hauppauge, NY 11788 USA  
Tel: (631) 435-1110  
Fax: (631) 435-1824  
www.centrasemi.com

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